

## **isc** Silicon NPN Darlington Power Transistor

# 2SD1790

### DESCRIPTION

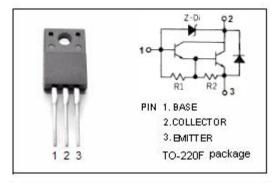
- Low Collector Saturation Voltage
- High DC Current Gain
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

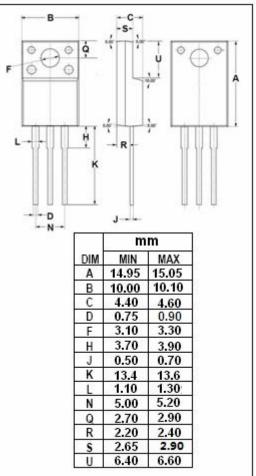
### APPLICATIONS

• Designed for audio frequency power amplifier and low speed high current switching industrial use.

ABSOLUTE MAXIMUM RATINGS( $T_a$ -25C)					
SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>CEO</sub>	Collector-Emitter Voltage	50-70	V		
V <sub>CBO</sub>	Collector-Base Voltage	50-70	V		
V <sub>EBO</sub>	Emitter-Base Voltage	7	V		
lc	Collector Current-Continunous	4	A		
I <sub>CM</sub>	Collector Current-Peak	6	А		
I <sub>B</sub>	Base Current-Continunous	0.3	А		
Івм	Base Current-Peak	0.5	А		
Pc	Collector Power Dissipation @T <sub>c</sub> =25℃	25	W		
Tj	Junction Temperature	150	°C		
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C		

#### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)





#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth j-c	Thermal Resistance, Junction to Case	5.0	°C/W



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 2mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 2mA			2.0	V
I <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			0.1	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 40V; I <sub>B</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			5	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A, V <sub>CE</sub> = 3V	1500		30000	
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.4A; V <sub>CE</sub> = 10V		20		MHz

Switching Times; Resistive Load

ton	Turn-On Time	I <sub>C</sub> = 1A; I <sub>B1</sub> = -I <sub>B2</sub> = 2mA V <sub>BB2</sub> = 4V; R <sub>L</sub> = 25 Ω		2	μS
ts	Storage Time			12	μ <b>s</b>
tf	Fall Time			5	μ S

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